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See also
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8/18/01

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-6. (Cancelled)

7. (Currently Amended) A silicon single crystal wafer which is a wafer prepared by means of a Czochralski method, the silicon single crystal wafer comprising at least one portion formed of an OSF ring portion in a peripheral region of the silicon single crystal wafer in contact with a boat on which the silicon single crystal wafer is placed for heat treatment.

8. (Previously Presented) A silicon single crystal wafer according to claim 7, wherein the OSF ring region is an annular region with a width of 10 mm or less from a periphery of the silicon single crystal wafer.

9. (Previously Presented) A silicon single crystal wafer according to claim 7, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

10. (Previously Presented) A silicon single crystal wafer according to claim 8, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

11. (Currently Amended) A manufacturing process for a silicon single crystal wafer comprising the steps of:

growing a silicon single crystal rod by means of a Czochralski method in a condition that an OSF ring region is formed in a peripheral region of the silicon single crystal rod; and

slicing the grown silicon single crystal rod into silicon single crystal wafers.